

# PNP Silicon High Voltage Transistor

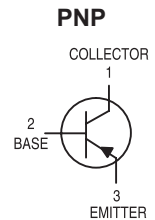
## 200V<sub>CEO</sub>, 1A I<sub>c</sub>

**multicomp** PRO

**RoHS  
Compliant**



TO-39



### Absolute Maximum Ratings

Description	Symbol	Value	Unit
Collector Emitter Voltage	V <sub>CEO</sub>	200	V
Collector Base Voltage	V <sub>CB0</sub>	200	V
Emitter Base Voltage	V <sub>EBO</sub>	4	V
Collector Current Continuous	I <sub>c</sub>	1	A
Base Current Continuous	I <sub>B</sub>	0.5	A
Power Dissipation at T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1	W
Power Dissipation at T <sub>c</sub> = 25°C Derate Above 25°C	P <sub>D</sub>	10	W
Operating and Storage Junction Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	200 -65 to +200	mW/°C °C
<b>Thermal Resistance</b>			
Junction to Ambient	R <sub>th(j-a)</sub>	150	°C/W
Junction to Case	R <sub>th(j-c)</sub>	17.5	°C/W

### Electrical Characteristics: (T<sub>A</sub> = +25°C Unless otherwise specified)

Description	Symbol	Test Conditions	Value	Unit
Collector Emitter Breakdown Voltage	BV <sub>CEO(sus)</sub> *	I <sub>c</sub> = 50mA, I <sub>B</sub> = 0	>200	V
Collector Cut off Current	I <sub>CB0</sub>	V <sub>CB</sub> = 175V, I <sub>E</sub> = 0	<50	μA
Collector Cutoff Current	I <sub>CEO</sub>	V <sub>CE</sub> = 150V, I <sub>B</sub> = 0	<50	μA
Emitter Cut off Current	I <sub>EBO</sub>	V <sub>EB</sub> = 4V, I <sub>c</sub> = 0	<20	μA
Collector Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> = 50mA, I <sub>B</sub> = 5mA	<2.5	V
Base Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>c</sub> = 50mA, I <sub>B</sub> = 5mA	<1.5	V
DC Current Gain	h <sub>FE</sub> *	I <sub>c</sub> = 50mA, V <sub>CE</sub> = 10V	30 - 150	

### Dynamic Characteristics

Small Signal Current Gain	h <sub>FE</sub>	I <sub>c</sub> = 5mA, V <sub>CE</sub> = 10V, f = 1kHz	>25	
Transition Frequency	f <sub>T</sub>	I <sub>c</sub> = 10mA, V <sub>CE</sub> = 10V, f = 5MHz	>15	MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MHz	<15	pF
Input Capacitance	C <sub>ib</sub>	V <sub>EB</sub> = V <sub>EB0max</sub> , I <sub>c</sub> = 0, f = 1MHz	<75	pF

\*Pulse Test: Pulse Width <300μs, Duty Cycle <2%

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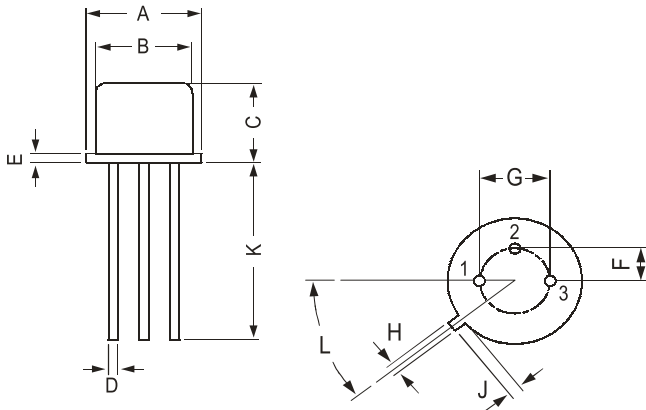
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## 200V<sub>CEO</sub>, 1A I<sub>c</sub>



### TO-39 Metal Can Package



Dim.	Min.	Max.
A	8.5	9.39
B	7.74	8.5
C	6.09	6.6
D	0.4	0.53
E	-	0.88
F	2.41	2.66
G	4.82	5.33
H	0.71	0.86
J	0.73	1.02
K	12.7	-
L	42 Deg.	48 Deg.

Dimensions : Millimetres

### Part Number Table

Description	Part Number
PNP Silicon High Voltage Transistor, 200V, 1A, TO-39	MP001173

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